

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI ULBM2TE is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	0.40 A
<b>V<sub>CB0</sub></b>	36 V
<b>V<sub>CEO</sub></b>	16 V
<b>V<sub>EBO</sub></b>	4.0 V
<b>P<sub>DISS</sub></b>	5 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	35 °C/W

**PACKAGE STYLE TO-39GE**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.200 / 5.080	
B	.029 / 0.740	.045 / 1.140
C	.028 / 0.720	.034 / 0.860
D	.355 / 9.020	.370 / 9.370
E	.315 / 8.010	.335 / 8.500
F	.165 / 4.200	.180 / 4.570
G	.500 / 12.700	.750 / 19.050
H	.016 / 0.410	.020 / 0.508

**ORDER CODE: ASI10679**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 50 mA	16			<b>V</b>
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 50 mA      R <sub>BE</sub> = 10 Ω	36			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1.0 mA	4.0			<b>V</b>
<b>I<sub>CB0</sub></b>	V <sub>CB</sub> = 15 V			1.0	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 50 mA	20		200	<b>---</b>
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 12.5 V      f = 1.0 MHz			10	<b>pF</b>
<b>P<sub>G</sub></b>	V <sub>CE</sub> = 12.5 V      P <sub>OUT</sub> = 2.0 W      f = 470 MHz	8.0			<b>dB</b>
<b>η<sub>c</sub></b>			55		<b>%</b>